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## (54) TARGET FOR SPUTTERING AND PRODUCTION ITS

## (57)Abstract:

PURPOSE: To provide a target which does not generate a drift in the compsn. ratio of a formed thin film with one piece by changing the mixing ratios of two kinds of materials continuously in the thickness direction of the target.

CONSTITUTION: After a target mold c7 is placed on an oscillation table 8, a target mold b6 is combined therewith and a uniformly mixed target material 4 is put therein; thereafter, the oscillation table 8 is oscillated. As a result, the sp. gr. of the target material 4 varies between two kinds of the materials and, therefore, the heavier material is moved perpendicularly downward and the lighter material is moved in the opposite direction. The target material 4 changed continuously in such a manner that the material of the higher sputtering rate

increases in the thickness direction is, therefore, obtd. This material is then subjected to pressurized sintering at the temp. lower by  $\geq 100^{\circ}\text{C}$  than the m.p. thereof or is subjected to the pressurized sintering at the above mentioned temp. after pressurization.

